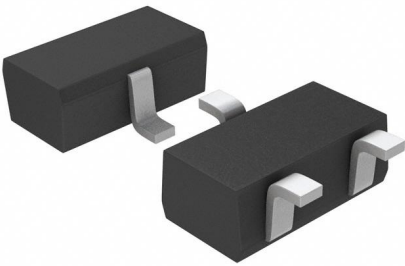


UNR31A1G0L Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	UNR31A1G0L-DG
Manufacturer	Panasonic Electronic Components
Manufacturer Product Number	UNR31A1G0L
Description	TRANS PREBIAS PNP 50V SSSMINI3
Detailed Description	Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biased 50 V 80 mA 80 MHz 100 mW Surface Mount SSSM ini3-F2



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

UNR31A1G0L

Series:

-

Transistor Type:

PNP - Pre-Biased

Voltage - Collector Emitter Breakdown (Max):

50 V

Resistor - Emitter Base (R2):

10 kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 300µA, 10mA

Frequency - Transition:

80 MHz

Mounting Type:

Surface Mount

Supplier Device Package:

SSSMini3-F2

Manufacturer:

Panasonic Electronic Components

Product Status:

Obsolete

Current - Collector (Ic) (Max):

80 mA

Resistor - Base (R1):

10 kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

35 @ 5mA, 10V

Current - Collector Cutoff (Max):

500nA

Power - Max:

100 mW

Package / Case:

SOT-723

Base Product Number:

UNR31

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

HTSUS:

8541.21.0095

ECCN:

EAR99

UNR31A1G

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Suitable for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

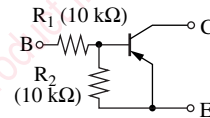
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_{C}	-80	mA
Total power dissipation	P_{T}	100	mW
Junction temperature	T_{j}	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Package

- Code
SSSMini3-F2
- Marking Symbol: CE
- Pin Name
1: Base
2: Emitter
3: Collector

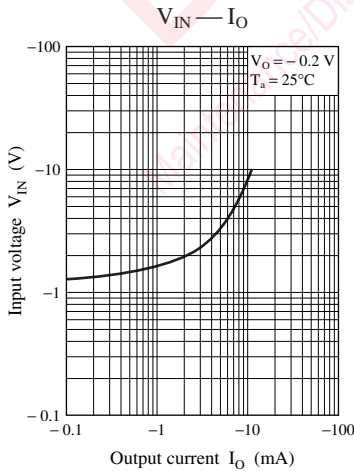
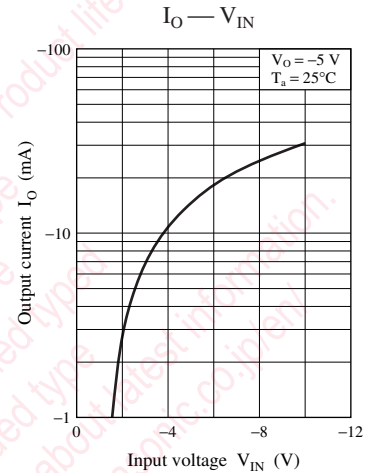
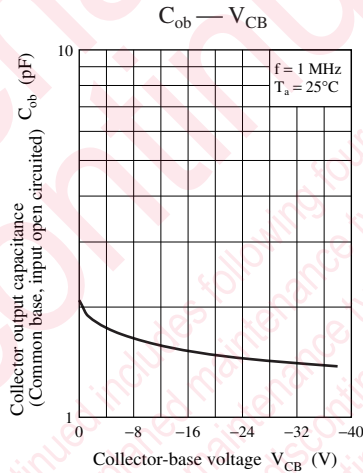
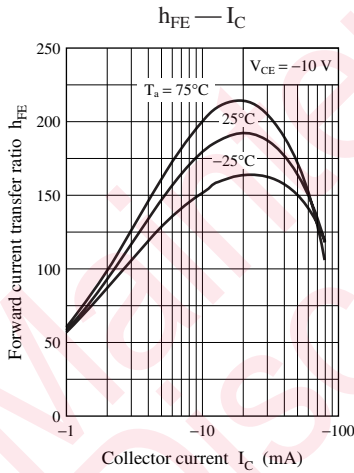
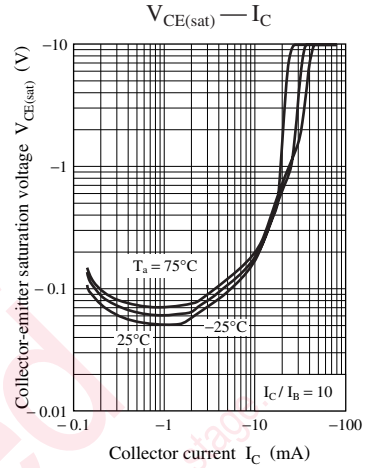
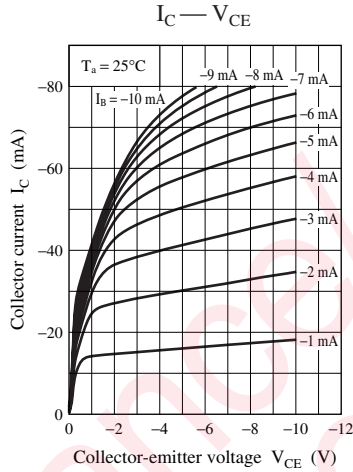
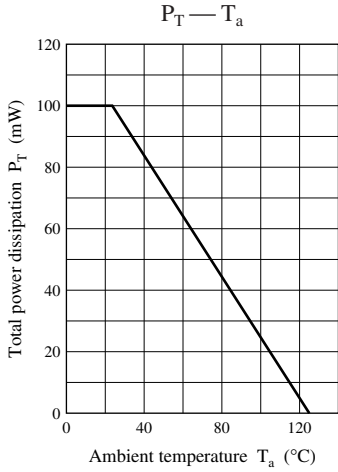
■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

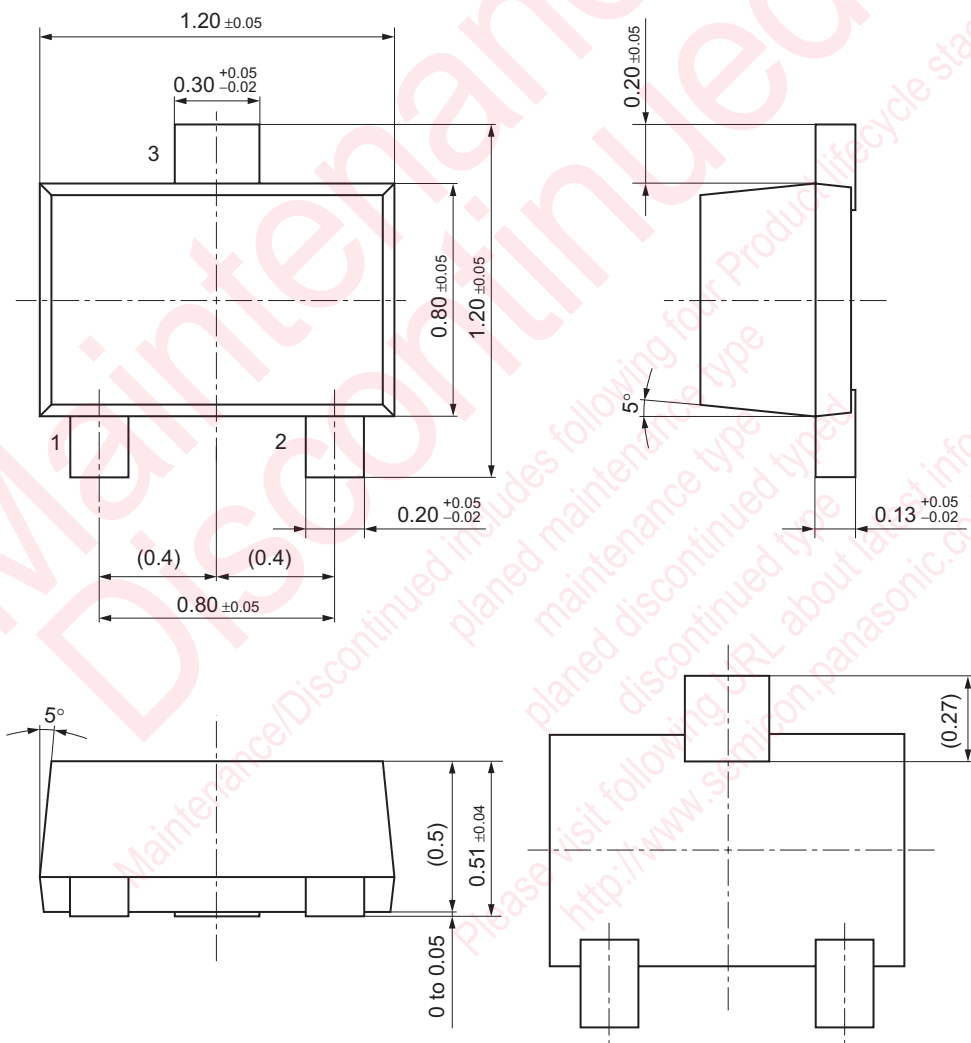
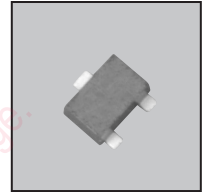
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -2 \text{ mA}, I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -50 \text{ V}, I_{\text{E}} = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{\text{CE}} = -50 \text{ V}, I_{\text{B}} = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\text{EB}} = -6 \text{ V}, I_{\text{C}} = 0$			-0.5	mA
Forward current transfer ratio	h_{FE}	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -5 \text{ mA}$	35			—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{ mA}, I_{\text{B}} = -0.3 \text{ mA}$			-0.25	V
Output voltage high-level	V_{OH}	$V_{\text{CC}} = -5 \text{ V}, V_{\text{B}} = -0.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{\text{CC}} = -5 \text{ V}, V_{\text{B}} = -2.5 \text{ V}, R_{\text{L}} = 1 \text{ k}\Omega$			-0.2	V
Input resistance	R_{I}		-30%	10	+30%	$\text{k}\Omega$
Resistance ratio	$R_{\text{I}} / R_{\text{2}}$		0.8	1.0	1.2	—
Transition frequency	f_{T}	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSSMINI3-F2

Unit: mm



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